

9097250 TOSHIBA (DISCRETE/OPTO)
 查 9097250 供应商
 SILICON NPN EPITAXIAL TYPE (PCT PROCESS)
 (DARLINGTON POWER)

56C 07974 0 T-33-07

2SD1438

MICRO MOTOR DRIVE, HAMMER DRIVE APPLICATIONS.
 SWITCHING APPLICATIONS.
 POWER AMPLIFIER APPLICATIONS.

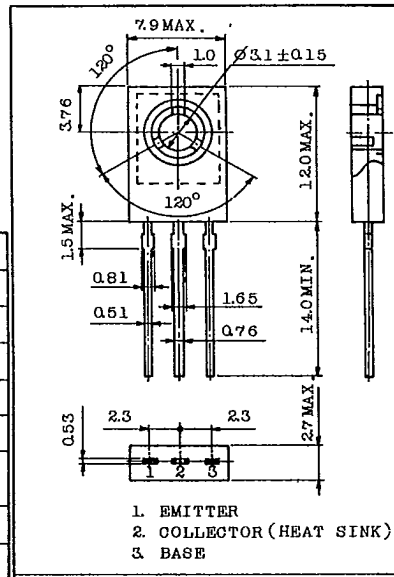
INDUSTRIAL APPLICATIONS
 Unit in mm

FEATURES:

- High DC Current Gain
 : $h_{FE}=2000$ (Min.) ($V_{CE}=2V, I_C=1A$)
- Low Saturation Voltage
 : $V_{CE(sat)}=1.5V$ (Max.) ($I_C=1A, I_B=1mA$)

MAXIMUM RATINGS ($T_a=25^\circ C$)

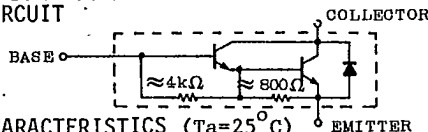
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	80	V
Collector-Emitter Voltage	V_{CEO}	80	V
Emitter-Base Voltage	V_{EBO}	8	V
Collector Current	I_C	2	A
Base Current	I_B	0.5	A
Collector Power Dissipation ($T_c=25^\circ C$)	P_C	15	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55 ~ 150	$^\circ C$



JEDEC	TO-126
EIAJ	-
TOSHIBA	2-8F1A

Mounting Kit No. AC46C
 Weight : 0.72g

EQUIVALENT CIRCUIT



ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=80V, I_E=0$	-	-	10	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=8V, I_C=0$	-	-	4	mA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=10mA, I_B=0$	80	-	-	V
DC Current Gain	h_{FE}	$V_{CE}=2V, I_C=1A$	2000	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=1A, I_B=1mA$	-	-	1.5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=1A, I_B=1mA$	-	-	2.0	V
Transition Frequency	f_T	$V_{CE}=2V, I_C=0.5A$	-	100	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$	-	20	-	pF
Switching Time	Turn-on Time	t_{on}	-	0.4	-	μs
	Storage Time	t_{stg}	-	4.0	-	
	Fall Time	t_f	-	0.6	-	

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